

#### **Feature**

- High Precision GaAs process
- High performance, shielded
- GaAs substrate, 50Ω CPW output
- Au wire bonding, for MCM applications

## **Environmental Specifications**

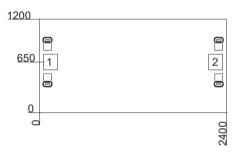
Operating Temperature	-55℃~+85℃	
Storage Temperature	-65°C∼+150°C	
Max. Input Power	30dBm	

# Electrical Specifications(T<sub>A</sub>=+25°C)

Parameter	Min.	Тур.	Max.	Unit
Center Freq. (f₀)	-	17	-	GHz
Pass band	16.5	=	17.5	GHz
Insertion Loss @ f <sub>0</sub>	-	=	4.0	dB
Ripple in Pass band	-	=	1	dB
Return Loss	12	=	1	dB
Out of band	≥30@15GHz			dB
Attenuation	≥30@19.1GHz			dB

S2P file name: PDBF-16R5\_17R5-5D3.s2p

## **Outline Drawing**

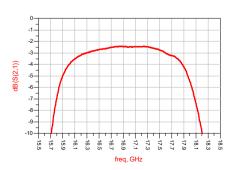


#### Notes:

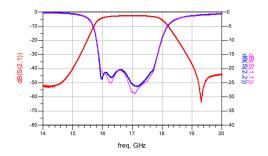
- 1. Dimensions are in millimeters. Tolerance:  $\pm 0.05 \text{mm}$
- 2. Die thickness is 0.15 mm
- 3. Typical bond pad is 0.1x0.1 mm<sup>2</sup>.
- 4. The bottom of the device is gold plated, should be grounded.

### **Typical Test Curves**

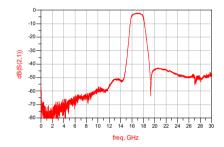
Insertion Loss VS Frequency (T<sub>A</sub>=25°C)



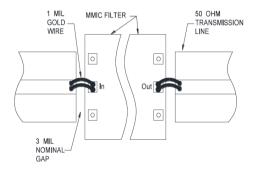
Insertion Loss & Return Loss VS Frequency (T<sub>A</sub>=25°C)



Broadband Insertion Loss VS Frequency (T<sub>A</sub>=25°C)



### **Recommended Assembly Diagrams**



### **Application Notes:**

- 1. The chip is back-metallized and can be die-mounted with AuSn eutectic preforms or with electrically conductive epoxy.
- 2. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (5.8×10-6/) with GaAs.
- 3. Recommend using  $\Phi 25 \text{um}$  Au wire for bonding, whose length is around 400 um.
- 4. Sinter by AuSn (80/20), which doesn't exceed 300°C within 30 seconds max.
- 4. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
- 5. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.
- 6. The device is sensitive to ESD. ESD protection is required during storage and usage.
- 7. If you have any questions, please contact us.